Tetsu Tanaka

List of Publications by Year in descending order

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300 papers

4,365 citations

279701 23 h-index 54 g-index

302 all docs 302 docs citations

302 times ranked 2766 citing authors

#	Article	IF	CITATIONS
1	Left ventricular apical pseudoaneurysm with shunt to the right ventricle following transapical aortic valve replacement. Cardiovascular Intervention and Therapeutics, 2022, 37, 412-413.	1.2	O
2	Autopsy findings of left atrial appendage closure device. Cardiovascular Pathology, 2022, 56, 107384.	0.7	2
3	Early response of right-ventricular function to percutaneous mitral valve repair. Clinical Research in Cardiology, 2022, 111, 859-868.	1.5	5
4	Room-Temperature Cu Direct Bonding Technology Enabling 3D Integration with Micro-LEDs. , 2022, , .		5
5	Multimodal Functional Analysis Platform: 4. Optogenetics-Induced Oscillatory Activation to Explore Neural Circuits. Advances in Experimental Medicine and Biology, 2021, 1293, 501-509.	0.8	O
6	Multimodal Functional Analysis Platform: 2. Development of Si Opto-Electro Multifunctional Neural Probe with Multiple Optical Waveguides and Embedded Optical Fiber for Optogenetics. Advances in Experimental Medicine and Biology, 2021, 1293, 481-491.	0.8	0
7	Prognostic impact of electrocardiographic left ventricular hypertrophy following transcatheter aortic valve replacement. Journal of Cardiology, 2021, 77, 346-352.	0.8	7
8	Prognostic significance of the get with the guidelines-heart failure (GWTG-HF) risk score in patients undergoing trans-catheter tricuspid valve repair (TTVR). Heart and Vessels, 2021, 36, 1903-1910.	0.5	3
9	Wafer-Level Flexible 3D Corrugated Interconnect Formation for Scalable In-Mold Electronics with Embedded Chiplets., 2021,,.		2
10	FOWLP-Based Flexible Hybrid Electronics with 3D-IC Chiplets for Smart Skin Display. , 2021, , .		6
11	Prognostic value of hepatorenal function following transcatheter edge-to-edge mitral valve repair. Clinical Research in Cardiology, 2021, 110, 1947-1956.	1.5	2
12	Development of Manganese Nitride Resistor with Near-Zero Temperature-Coefficient of Resistance to Achieve High-Thermal-Stability ICs. , $2021, \ldots$		2
13	Prognostic impact of arterial stiffness following transcatheter aortic valve replacement. Journal of Cardiology, 2021, 78, 37-43.	0.8	7
14	Prognostic impact of hepatorenal function in patients undergoing transcatheter tricuspid valve repair. Scientific Reports, 2021, 11, 14420.	1.6	7
15	Leaflet Configuration and Residual Tricuspid Regurgitation After Transcatheter Edge-to-Edge TricuspidÂRepair. JACC: Cardiovascular Interventions, 2021, 14, 2260-2270.	1.1	30
16	High-thermal-stability resistor formed from manganese nitride compound that exhibits the saturation state of the mean free path. Applied Physics Express, 2021, 14, 091003.	1.1	3
17	Periprocedural changes in natriuretic peptide levels and clinical outcome after transcatheter mitral valve repair. ESC Heart Failure, 2021, , .	1.4	2
18	The role of the renal resistance index in patients with heart failure with reduced or preserved ejection fraction. Journal of Cardiology, 2021, 78, 301-307.	0.8	4

#	Article	lF	Citations
19	Direct Fabrication of SU-8 Microchannel across an Embedded Chip for Potentiometric Bilayer Lipid Membrane Sensor. IEEJ Transactions on Sensors and Micromachines, 2021, 141, 327-335.	0.0	1
20	Multimodal Functional Analysis Platform: 1. Ultrathin Fluorescence Endoscope Imaging System Enables Flexible Functional Brain Imaging. Advances in Experimental Medicine and Biology, 2021, 1293, 471-479.	0.8	1
21	Multimodal Functional Analysis Platform: 3. Spherical Treadmill System for Small Animals. Advances in Experimental Medicine and Biology, 2021, 1293, 493-500.	0.8	1
22	Integration of Damage-less Probe Cards Using Nano-TSV Technology for Microbumped Wafer Testing. , 2021, , .		4
23	Design and Evaluation of Electronic-Microsaccade with Balanced Stimulation for Artificial Vision System., 2021,,.		1
24	Multichip thinning technology with temporary bonding for multichip-to-wafer 3D integration. Japanese Journal of Applied Physics, 2020, 59, SBBA04.	0.8	3
25	The impact of tissue-tracking strain on the left atrial dysfunction in the patients with left ventricular dysfunction. IJC Heart and Vasculature, 2020, 26, 100453.	0.6	O
26	Symmetric and asymmetric spike-timing-dependent plasticity function realized in a tunnel-field-effect-transistor-based charge-trapping memory. Japanese Journal of Applied Physics, 2020, 59, SGGB12.	0.8	2
27	Corroborative Autopsy Findings for Current Concerns After Implantation ofÂSelf-Expandable Transcatheter HeartÂValve. JACC: Cardiovascular Interventions, 2020, 13, 261-262.	1.1	O
28	Generation of STDP With Non-Volatile Tunnel-FET Memory for Large-Scale and Low-Power Spiking Neural Networks. IEEE Journal of the Electron Devices Society, 2020, 8, 1266-1271.	1.2	3
29	Low-temperature multichip-to-wafer 3D integration based on via-last TSV with OER-TEOS-CVD and microbump bonding without solder extrusion. , 2020, , .		2
30	Acute Coronary Syndrome Due to Myeloperoxidase-Antineutrophil Cytoplasmic Antibody-Associated Vasculitis. JACC: Cardiovascular Interventions, 2020, 13, e215-e216.	1.1	2
31	RDL-first Flexible FOWLP Technology with Dielets Embedded in Hydrogel. , 2020, , .		5
32	Significant Die-Shift Reduction and $\langle i \rangle \hat{l}^{1}\!\!/4 \langle /i \rangle$ LED Integration Based on Die-First Fan-Out Wafer-Level Packaging for Flexible Hybrid Electronics. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2020, 10, 1419-1422.	1.4	5
33	$7-\hat{l}\frac{1}{4}$ m-thick NCF technology with low-height solder microbump bonding for 3D integration. , 2020, , .		2
34	Clinical Predictors of Coronary Artery Plaque Progression by Quantitative Serial Assessment Using 320-Row Computed Tomography Coronary Angiography in Asymptomatic Patients with Type 2 Diabetes Mellitus. Journal of Cardiology, 2020, 76, 378-384.	0.8	2
35	Development of Non-Volatile Tunnel-FET Memory as a Synaptic Device for Low-Power Spiking Neural Networks. , 2020, , .		1
36	Efficacy of catheter-based renal denervation in the absence of antihypertensive medications (SPYRAL) Tj ETQq0 1444-1451.	0 0 rgBT /0 6.3	Overlock 10 Tf 351

1444-1451.

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37	<scp>Onâ€wafer</scp> thermomechanical characterization of a thin film polyimide formed by vapor deposition polymerization for <scp>throughâ€silicon</scp> via applications: Comparison to <scp>plasmaâ€enhanced</scp> chemical vapor deposition <scp>SiO₂</scp> . Journal of Polymer Science, 2020, 58, 2248-2258.	2.0	5
38	Mechanical Characterization of FOWLPB ased Flexible Hybrid Electronics (FHE) for Biomedical Sensor Application. , 2019, , .		0
39	Mechanical and Electrical Characterization of FOWLP-Based Flexible Hybrid Electronics (FHE) for Biomedical Sensor Application. , 2019, , .		6
40	Investigation of TSV Liner Interface With Multiwell Structured TSV to Suppress Noise Propagation in Mixed-Signal 3D-IC. IEEE Journal of the Electron Devices Society, 2019, 7, 1225-1231.	1.2	6
41	Noise Propagation through TSV in Mixed-Signal 3D-IC and Investigation of Liner Interface with Multi-Well Structured TSV. , 2019, , .		1
42	Development of Eccentric Spin Coating of Polymer Liner for Low-Temperature TSV Technology With Ultra-Fine Diameter. IEEE Electron Device Letters, 2019, 40, 95-98.	2.2	14
43	Impact of abdominal fat distribution, visceral fat, and subcutaneous fat on coronary plaque scores assessed by 320-row computed tomography coronary angiography. Atherosclerosis, 2019, 287, 155-161.	0.4	23
44	The Effect of Tungsten Volume on Residual Stress and Cell Characteristics in MONOS. IEEE Journal of the Electron Devices Society, 2019, 7, 382-387.	1,2	2
45	Investigation of the Impact of External Stress on Memory Characteristics by Modifying the Backside of Substrate. IEEE Transactions on Electron Devices, 2019, 66, 1741-1746.	1.6	1
46	Evaluation of objective nutritional indexes as predictors of one-year outcomes after transcatheter aortic valve implantation. Journal of Cardiology, 2019, 74, 34-39.	0.8	32
47	The role of transcatheter aortic valve replacement in the patients with severe aortic stenosis requiring major non-cardiac surgery. Cardiovascular Intervention and Therapeutics, 2019, 34, 345-351.	1.2	11
48	Investigation of the Underfill with Negative-Thermal-Expansion Material to Suppress Mechanical Stress in 3D Integration System. , 2019, , .		1
49	PPG and SpO ₂ Recording Circuit with Ambient Light Cancellation for Trans-Nail Pulse-Wave Monitoring System., 2019,,.		5
50	Characterization of Low-Height Solder Microbump Bonding for Fine-Pitch Inter-Chip Connection in 3DICs., 2019,,.		2
51	Impacts of Deposition Temperature and Annealing Condition on Ozone-Ethylene Radical Generation-TEOS-CVD SiO2 for Low-Temperature TSV Liner Formation. , 2019, , .		0
52	Multichip thinning technology with temporary bonding for multichip-to-wafer 3D integration. , 2019, , .		0
53	Development of 3D-IC Embedded Flexible Hybrid System. , 2019, , .		2
54	Immunoglobulin G4-Related CoronaryÂPeriarteritis With MultipleÂIntracoronary Images. JACC: Cardiovascular Interventions, 2019, 12, e59-e61.	1.1	9

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55	High-Thermoresistant Temporary Bonding Technology for Multichip-to-Wafer 3-D Integration With Via-Last TSVs. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2019, 9, 181-188.	1.4	5
56	Development of integrated photoplethysmographic recording circuit for trans-nail pulse-wave monitoring system. Japanese Journal of Applied Physics, 2018, 57, 04FM11.	0.8	6
57	Identifying novel phenotypes of acute heart failure using cluster analysis of clinical variables. International Journal of Cardiology, 2018, 262, 57-63.	0.8	55
58	Tunnel field-effect transistor charge-trapping memory with steep subthreshold slope and large memory window. Japanese Journal of Applied Physics, 2018, 57, 04FE07.	0.8	6
59	Development of Biosignal Recording Board System with Agile Control of Circuit Characteristics for Various Biosignals. Electronics and Communications in Japan, 2018, 101, 47-54.	0.3	6
60	Hemodynamic correlates of nutritional indexes in heart failure. Journal of Cardiology, 2018, 71, 557-563.	0.8	12
61	Process Integration for FlexTrate TM ., 2018,,.		2
62	ST-Segment Elevation Myocardial Infarction Related to Variable Calcified Lesions in Saphenous Vein Graft 33 Years After Coronary Artery Bypass Grafting. JACC: Cardiovascular Interventions, 2018, 11, e181-e183.	1.1	2
63	Continuous Peripheral Blood Pressure Measurement with ECG and PPG Signals at Fingertips. , 2018, , .		3
64	Prognostic Impact of Computed Tomography-Derived Abdominal Fat Area on Transcatheter Aortic Valve Implantation. Circulation Journal, 2018, 82, 3082-3089.	0.7	11
65	The Effect of Mechanical Stress on Cell Characteristics in MONOS Structures. IEEE Transactions on Electron Devices, 2018, 65, 4313-4319.	1.6	4
66	Charge-Trap-Free Polymer-Liner Through-Silicon Vias for Reliability Improvement of 3D ICs., 2018, , .		6
67	Efficacy of Pericardial Drainage in Annular Rupture and Periaortic Hematoma After Transcatheter Aortic Valve Replacement. Circulation Journal, 2018, 83, 241-242.	0.7	1
68	Self-Assembly Technologies for FlexTrateâ,,¢., 2018,,.		6
69	Transcatheter aortic valve implantation in a patient with severe aortic valve stenosis, colon cancer, and obstructive ileus: A case report. Journal of Cardiology Cases, 2018, 17, 163-166.	0.2	6
70	Study of Al-doped ZnO Transparent Stimulus Electrode for Fully Implantable Retinal Prosthesis with Three-dimensionally Stacked Retinal Prosthesis Chip. Sensors and Materials, 2018, , 225.	0.3	6
71	Evaluation of insertion characteristics of less invasive Si optoneural probe with embedded optical fiber. Japanese Journal of Applied Physics, 2017, 56, 04CM08.	0.8	1
72	3D-IC technology and reliability challenges. , 2017, , .		5

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73	3-D Sidewall Interconnect Formation Climbing Over Self-Assembled KGDs for Large-Area Heterogeneous Integration. IEEE Transactions on Electron Devices, 2017, 64, 2912-2918.	1.6	5
74	Minimized hysteresis and low parasitic capacitance TSV with PBO (polybenzoxazole) liner to achieve ultra-high-speed data transmission. , 2017, , .		4
75	Ultrawide range square wave impedance analysis circuit with ultra-slow ring-oscillator using gate-induced drain-leakage current. , 2017, , .		0
76	Design and evaluation of wide-range and low-power analog front-end enabling body-implanted devices to monitor charge injection properties. Japanese Journal of Applied Physics, 2017, 56, 04CM05.	0.8	0
77	Development of Si neural probe with piezoresistive force sensor for minimally invasive and precise monitoring of insertion forces. Japanese Journal of Applied Physics, 2017, 56, 04CM04.	0.8	0
78	Self-Assembly and Electrostatic Carrier Technology for Via-Last TSV Formation Using Transfer Stacking-Based Chip-to-Wafer 3-D Integration. IEEE Transactions on Electron Devices, 2017, 64, 5065-5072.	1.6	11
79	Experimental evaluation of stimulus current generator with Laplacian edge-enhancement for 3-D stacked retinal prosthesis chip. , 2017, , .		6
80	Remarkable Suppression of Local Stress in 3D IC by Manganese Nitride-Based Filler with Large Negative CTE. , $2017, \dots$		19
81	Development of Biosignal Recording Board System with Agile Control of Circuit Characteristics for Various Biosignals. IEEJ Transactions on Electronics, Information and Systems, 2017, 137, 348-353.	0.1	0
82	Evaluation of in-plane local stress distribution in stacked IC chip using dynamic random access memory cell array for highly reliable three-dimensional IC. Japanese Journal of Applied Physics, 2016, 55, 04EC07.	0.8	1
83	Oxide-Oxide Thermocompression Direct Bonding Technologies with Capillary Self-Assembly for Multichip-to-Wafer Heterogeneous 3D System Integration. Micromachines, 2016, 7, 184.	1.4	17
84	Effect of local stress induced by thermal expansion of underfill in three-dimensional stacked IC. Japanese Journal of Applied Physics, 2016, 55, 04EC03.	0.8	8
85	Improving the integrity of Ti barrier layer in Cu-TSVs through self-formed TiSi <inf>x</inf> for via-last TSV technology. , 2016, , .		0
86	Nano-scale Cu direct bonding using ultra-high density Cu nano-pillar (CNP) for high yield exascale 2.5/3D integration applications. , 2016, , .		0
87	Transfer and Non-transfer 3D Stacking Technologies Based on Multichip-to-Wafer Self-Assembly and Direct Bonding. , 2016, , .		2
88	Impact of local stress in 3D stacking process on memory retention characteristics in thinned DRAM chip. , 2016, , .		0
89	Novel W2W/C2W Hybrid Bonding Technology with High Stacking Yield Using Ultra-Fine Size, Ultra-High Density Cu Nano-Pillar (CNP) for Exascale 2.5D/3D Integration., 2016,,.		2
90	Impact of Interconnections on Vertically Stacked 20 um-Thick DRAM Chips., 2016,,.		0

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91	Wide-range and precise tissue impedance analysis circuit with ultralow current source using gate-induced drain-leakage current. , 2016, , .		1
92	Heterogeneous 3-D Integration Using Self-Assembly and Electrostatic Bonding. IEEE Transactions on Components, Packaging and Manufacturing Technology, 2016, 6, 1000-1006.	1.4	5
93	(Invited) Self-Assembly Based Multichip-to-Wafer Bonding Technologies for 3D/Hetero Integration. ECS Transactions, 2016, 75, 285-290.	0.3	O
94	Highly sensitive pressure sensor with silicon-on-nothing (SON) MOSFET for sensor integrated heterogeneous system. , 2016, , .		0
95	Design and evaluation of area-efficient and wide-range impedance analysis circuit for multichannel high-quality brain signal recording system. Japanese Journal of Applied Physics, 2016, 55, 04EM12.	0.8	4
96	New concept of TSV formation methodology using Directed Self-Assembly (DSA). , 2016, , .		3
97	Drastic reduction of keep-out-zone in 3D-IC by local stress suppression with negative-CTE filler. , 2016, , .		1
98	Capillary Self-Assembly for 3D Heterogeneous System Integration and Packaging. MRS Advances, 2016, 1, 2355-2366.	0.5	10
99	Back-via 3D integration technologies by temporary bonding with thermoplastic adhesives and visible-laser debonding. , 2016 , , .		3
100	Impact of Chip-Edge Structures on Alignment Accuracies of Self-Assembled Dies for Microelectronic System Integration. Journal of Microelectromechanical Systems, 2016, 25, 91-100.	1.7	9
101	Novel Hybrid Bonding Technology Using Ultra-High Density Cu Nano-Pillar for Exascale 2.5D/3D Integration. IEEE Electron Device Letters, 2016, 37, 81-83.	2.2	4
102	Reconfigured multichip-on-wafer (mCoW) Cu/oxide hybrid bonding technology for ultra-high density 3D integration using recessed oxide, thin glue adhesive, and thin metal capping layers. , 2015, , .		4
103	Advanced 2.5D/3D hetero-integration technologies at GINTI, Tohoku University. , 2015, , .		0
104	Consideration of microbump layout for reduction of local bending stress due to CTE Mismatch in 3D IC. , 2015, , .		2
105	Novel reconfigured wafer-to-wafer (W2W) hybrid bonding technology using ultra-high density nano-Cu filaments for exascale 2.5D/3D integration. , 2015 , , .		7
106	Transfer and non-transfer stacking technologies based on chip-to-wafer self-asembly for high-throughput and high-precision alignment and microbump bonding. , $2015, \ldots$		1
107	Impact of deep-via plasma etching process on transistor performance in 3D-IC with via-last backside TSV. , 2015, , .		2
108	Novel local stress evaluation method in 3D IC using DRAM cell array with planar mOS capacitors. , 2015, , .		1

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109	Role of Bath Composition in Electroless Cu Seeding on Co Liner for through-Si Vias. ECS Journal of Solid State Science and Technology, 2015, 4, N3108-N3112.	0.9	7
110	Vertical-cavity surface-emitting laser chip bonding by surface-tension-driven self-assembly for optoelectronic heterogeneous integration. Japanese Journal of Applied Physics, 2015, 54, 030206.	0.8	8
111	Applications of three-dimensional LSI. MRS Bulletin, 2015, 40, 242-247.	1.7	8
112	Impacts of 3-D integration processes on device reliabilities in thinned DRAM chip for 3-D DRAM., 2015,,.		1
113	Development of highly-reliable microbump bonding technology using self-assembly of NCF-covered KGDs and multi-layer 3D stacking challenges. , 2015, , .		10
114	Plasma assisted multichip-to-wafer direct bonding technology for self-assembly based 3D integration. , 2015, , .		5
115	Reconfigured-Wafer-to-Wafer 3-D Integration Using Parallel Self-Assembly of Chips With Cu–SnAg Microbumps and a Nonconductive Film. IEEE Transactions on Electron Devices, 2014, 61, 533-539.	1.6	41
116	Deteriorated Device Characteristics in 3D-LSI Caused by Distorted Silicon Lattice. IEEE Transactions on Electron Devices, 2014, 61, 540-547.	1.6	8
117	Envelope tracking CMOS power amplifier with high-speed CMOS envelope amplifier for mobile handsets. Japanese Journal of Applied Physics, 2014, 53, 04EE19.	0.8	0
118	Minimization of Keep-Out-Zone (KOZ) in 3D IC by local bending stress suppression with low temperature curing adhesive. , 2014, , .		5
119	Fabrication and Testing of a Bi-Conductive Polymer Membrane Fuel Cell. Journal of Physics: Conference Series, 2014, 557, 012007.	0.3	1
120	Effects of electro-less Ni layer as barrier/seed layers for high reliable and low cost Cu TSV., 2014,,.		5
121	Tiny VCSEL chip self-assembly for advanced chip-to-wafer 3D and hetero integration. , 2014, , .		1
122	Cu seeding using electroless deposition on Ru liner for high aspect ratio through-Si vias. , 2014, , .		2
123	Micro-XRD investigation of fine-pitch Cu-TSV induced thermo-mechanical stress in high-density 3D-LSI. , 2014, , .		2
124	A new temporary bonding technology with spin-on glass and hydrogenated amorphous Si for 3D LSIs. , 2014, , .		3
125	Direct multichip-to-wafer 3D integration technology using flip-chip self-assembly of NCF-covered known good dies. , 2014, , .		13
126	Solid State Devices and Materials. Japanese Journal of Applied Physics, 2014, 53, 04E001.	0.8	3

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127	Highly dependable 3-D stacked multicore processor system module fabricated using reconfigured multichip-on-wafer 3-D integration technology. , 2014 , , .		2
128	Nucleation Kinetics of Electroless Cu Deposition on Ruthenium Using Glyoxylic Acid as a Reducing Agent. Journal of the Electrochemical Society, 2014, 161, D768-D774.	1.3	14
129	Temporary spin-on glass bonding technologies for via-last/backside-via 3D integration using multichip self-assembly. , 2014, , .		8
130	Barrier Properties of CVD Mn Oxide Layer to Cu Diffusion for 3-D TSV. IEEE Electron Device Letters, 2014, 35, 114-116.	2.2	19
131	Impacts of Cu contamination in 3D integration process on memory retention characteristics in thinned DRAM chip. , 2014, , .		7
132	Impacts of 3-D Integration Processes on Memory Retention Characteristics in Thinned DRAM Chip for High-Reliable 3-D DRAM. IEEE Transactions on Electron Devices, 2014, 61, 379-385.	1.6	15
133	Impacts of Cu Contamination on Device Reliabilities in 3-D IC Integration. IEEE Transactions on Device and Materials Reliability, 2014, 14, 451-462.	1.5	14
134	Replacing the PECVD-SiO <inf>2</inf> in the through-silicon via of high-density 3D LSIs with highly scalable low cost organic liner: Merits and demerits. , 2014, , .		7
135	Surface-tension driven self-assembly for VCSEL chip bonding to achieve 3D and hetero integration. , 2014, , .		0
136	Highly thermoresistant temporary bonding/debonding system without organic adhesives for 3D integration. , 2014, , .		2
137	A resilient 3-D stacked multicore processor fabricated using die-level 3-D integration and backside TSV technologies. , 2014, , .		6
138	Electroless Cu seed on Ru and Co liners in high aspect ratio TSV. , 2014, , .		2
139	Via Reveal and Backside Processing. , 2014, , 227-240.		0
140	3D hetero-integration technology with backside TSV and reliability challenges. , 2013, , .		0
141	Multiple optical stimulation to neuron using Si opto-neural probe with multiple optical waveguides and metal-cover for optogenetics., 2013, 2013, 253-6.		9
142	3D Integration technologies using self-assembly and electrostatic temporary multichip bonding. , 2013, , .		5
143	Impacts of static and dynamic local bending of thinned Si chip on MOSFET performance in 3-D stacked LSI. , 2013, , .		11
144	Mechanical characteristics of thin dies/wafers in three-dimensional large-scale integrated systems. , 2013, , .		7

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145	Degradation of Memory Retention Characteristics in DRAM Chip by Si Thinning for 3-D Integration. IEEE Electron Device Letters, 2013, 34, 1038-1040.	2.2	25
146	Characterization and reliability of 3D LSI and SiP. , 2013, , .		3
147	A block-parallel ADC with digital noise cancelling for 3-D stacked CMOS image sensor. , 2013, , .		3
148	Effect of CVD Mn oxide layer as Cu diffusion barrier for TSV., 2013,,.		2
149	(Invited) Challenges in 3D Integration. ECS Transactions, 2013, 53, 237-244.	0.3	1
150	Highly efficient TSV repair technology for resilient 3-D stacked multicore processor system., 2013,,.		4
151	Impact of 3-D integration process on memory retention characteristics in thinned DRAM chip for 3-D memory. , 2013, , .		3
152	Investigation of Local Bending Stress Effect on Complementary Metal–Oxide–Semiconductor Characteristics in Thinned Si Chip for Chip-to-Wafer Three-Dimensional Integration. Japanese Journal of Applied Physics, 2013, 52, 04CB11.	0.8	16
153	Fabrication and In vivo Evaluation of Poly(3,4-ethylenedioxythiophene) Stimulus Electrodes for Fully Implantable Retinal Prosthesis. Japanese Journal of Applied Physics, 2013, 52, 04CL03.	0.8	4
154	Study of Insertion Characteristics of Si Neural Probe with Sharpened Tip for Minimally Invasive Insertion to Brain. Japanese Journal of Applied Physics, 2013, 52, 04CL04.	0.8	2
155	Reductant-Assisted Self-Assembly with Cu/Sn Microbump for Three-Dimensional Heterogeneous Integration. Japanese Journal of Applied Physics, 2013, 52, 04CB09.	0.8	14
156	Die-Level 3-D Integration Technology for Rapid Prototyping of High-Performance Multifunctionality Hetero-Integrated Systems. IEEE Transactions on Electron Devices, 2013, 60, 3842-3848.	1.6	26
157	Flux-assisted self-assembly with microbump bonding for 3D heterogeneous integration. , 2013, , .		11
158	Non-conductive film and compression molding technology for self-assembly-based 3D integration. , 2012, , .		12
159	New chip-to-wafer 3D integration technology using hybrid self-assembly and electrostatic temporary bonding. , 2012, , .		18
160	Heterogeneous 3D integration technology and new 3D LSIs. , 2012, , .		0
161	Impact of Cu Contamination on Memory Retention Characteristics in Thinned DRAM Chip for 3-D Integration. IEEE Electron Device Letters, 2012, 33, 1297-1299.	2.2	14
162	Inhibition of lî [®] B phosphorylation prevents load-induced cardiac dysfunction in mice. American Journal of Physiology - Heart and Circulatory Physiology, 2012, 303, H1435-H1445.	1.5	17

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163	Multichip-to-Wafer Three-Dimensional Integration Technology Using Chip Self-Assembly With Excimer Lamp Irradiation. IEEE Transactions on Electron Devices, 2012, 59, 2956-2963.	1.6	44
164	Pillar-shaped stimulus electrode array for high-efficiency stimulation of fully implantable epiretinal prosthesis. Journal of Micromechanics and Microengineering, 2012, 22, 105015.	1.5	11
165	Novel detachable bonding process with wettability control of bonding surface for versatile chip-level 3D integration. , 2012, , .		4
166	W/Cu TSVs for 3D-LSI with minimum thermo-mechanical stress. , 2012, , .		4
167	Temporary bonding strength control for self-assembly-based 3D integration. , 2012, , .		1
168	HIGH ENDURANCE NON-VOLATILE SEMICONDUCTOR MEMORY FOR FULLY IMPLANTABLE RETINAL PROSTHESIS. , $2012, , .$		0
169	Characterization of chip-level hetero-integration technology for high-speed, highly parallel 3D-stacked image processing system. , 2012, , .		9
170	Thermomechanical reliability challenges induced by high density Cu TSVs and metal micro-joining for 3-D ICs. , 2012, , .		10
171	Study for CMOS device characteristics affected by ultra thin wafer thinning. , 2012, , .		0
172	Impact of Cu diffusion from Cu through-silicon via (TSV) on device reliability in 3-D LSIs evaluated by transient capacitance measurement. , 2012, , .		14
173	Chip-based hetero-integration technology for high-performance 3D stacked image sensor. , 2012, , .		5
174	Through-Silicon Photonic Via and Unidirectional Coupler for High-Speed Data Transmission in Optoelectronic Three-Dimensional LSI. IEEE Electron Device Letters, 2012, 33, 221-223.	2.2	22
175	High-step-coverage Cu-lateral interconnections over 100 µm thick chips on a polymer substrate—an alternative method to wire bonding. Journal of Micromechanics and Microengineering, 2012, 22, 085033.	1.5	8
176	Low-Resistance Cu-Sn Electroplated–Evaporated Microbumps for 3D Chip Stacking. Journal of Electronic Materials, 2012, 41, 720-729.	1.0	14
177	The Road to Recovery from the Great East Japan Earthquake in Micro/Nano Machining Research and Education Center, Tohoku University. Journal of the Vacuum Society of Japan, 2012, 55, 413-416.	0.3	0
178	DEVELOPMENT OF IN VIVO DOUBLE-SIDED SI NEURAL PROBE AND ION-SENSITIVE CAPACITOR FOR IMPLANTABLE SYSTEM. , 2012, , .		0
179	DEVELOPMENT OF OPTICAL MODULATOR ON S NEURAL PROBE FOR MULTIPLE OPTICAL STIMULATIONS OF NEURAL CELLS. , 2012, , .		0
180	DEVELOPMENT OF FINE SIZED CU THROUGH-SILICON VIAS FOR THREE-DIMENSIONAL STACKED RETINAL PROSTHESIS CHIP. , $2012,$, .		0

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